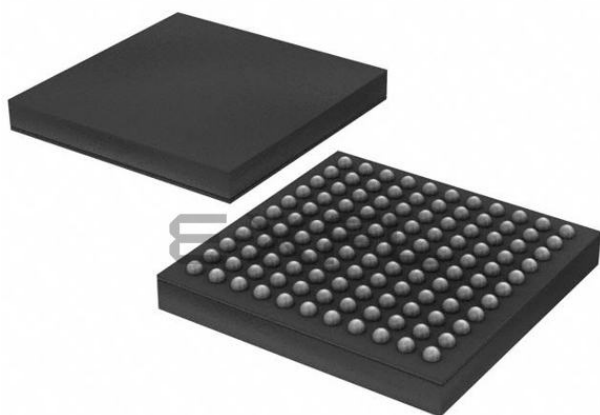




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"[Embedded - Microcontrollers](#)" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

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Details

Product Status	Discontinued at Digi-Key
Core Processor	ARM® Cortex®-M4F
Core Size	32-Bit Single-Core
Speed	48MHz
Connectivity	EBI/EMI, I ² C, IrDA, SmartCard, SPI, UART/USART
Peripherals	Brown-out Detect/Reset, DMA, I ² S, POR, PWM, WDT
Number of I/O	93
Program Memory Size	128KB (128K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	32K x 8
Voltage - Supply (Vcc/Vdd)	1.98V ~ 3.8V
Data Converters	A/D 8x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	120-VFBGA
Supplier Device Package	120-BGA (7x7)
Purchase URL	https://www.e-xfl.com/product-detail/silicon-labs/efm32wg295f128-bga120t

1 Ordering Information

Table 1.1 (p. 2) shows the available EFM32WG295 devices.

Table 1.1. Ordering Information

Ordering Code	Flash (kB)	RAM (kB)	Max Speed (MHz)	Supply Voltage (V)	Temperature (°C)	Package
EFM32WG295F64-BGA120	64	32	48	1.98 - 3.8	-40 - 85	BGA120
EFM32WG295F128-BGA120	128	32	48	1.98 - 3.8	-40 - 85	BGA120
EFM32WG295F256-BGA120	256	32	48	1.98 - 3.8	-40 - 85	BGA120

Visit **www.silabs.com** for information on global distributors and representatives.

Module	Configuration	Pin Connections
PRS	Full configuration	NA
EBI	Full configuration	EBI_A[27:0], EBI_AD[15:0], EBI_ARDY, EBI_ALE, EBI_BL[1:0], EBI_CS[3:0], EBI_CSTFT, EBI_DCLK, EBI_DTEN, EBI_HSNC, EBI_NANDREn, EBI_NANDWEn, EBI_REn, EBI_VSNC, EBI_WEn
I2C0	Full configuration	I2C0_SDA, I2C0_SCL
I2C1	Full configuration	I2C1_SDA, I2C1_SCL
USART0	Full configuration with IrDA	US0_TX, US0_RX, US0_CLK, US0_CS
USART1	Full configuration with I2S	US1_TX, US1_RX, US1_CLK, US1_CS
USART2	Full configuration with I2S	US2_TX, US2_RX, US2_CLK, US2_CS
UART0	Full configuration	U0_TX, U0_RX
UART1	Full configuration	U1_TX, U1_RX
LEUART0	Full configuration	LEU0_TX, LEU0_RX
LEUART1	Full configuration	LEU1_TX, LEU1_RX
TIMER0	Full configuration with DTI	TIM0_CC[2:0], TIM0_CDTI[2:0]
TIMER1	Full configuration	TIM1_CC[2:0]
TIMER2	Full configuration	TIM2_CC[2:0]
TIMER3	Full configuration	TIM3_CC[2:0]
RTC	Full configuration	NA
BURTC	Full configuration	NA
LETIMER0	Full configuration	LET0_O[1:0]
PCNT0	Full configuration, 16-bit count register	PCNT0_S[1:0]
PCNT1	Full configuration, 8-bit count register	PCNT1_S[1:0]
PCNT2	Full configuration, 8-bit count register	PCNT2_S[1:0]
ACMP0	Full configuration	ACMP0_CH[7:0], ACMP0_O
ACMP1	Full configuration	ACMP1_CH[7:0], ACMP1_O
VCMP	Full configuration	NA
ADC0	Full configuration	ADC0_CH[7:0]
DAC0	Full configuration	DAC0_OUT[1:0], DAC0_OUTxALT
OPAMP	Full configuration	Outputs: OPAMP_OUTx, OPAMP_OUTxALT, Inputs: OPAMP_Px, OPAMP_Nx
AES	Full configuration	NA
GPIO	93 pins	Available pins are shown in Table 4.3 (p. 67)

2.3 Memory Map

The *EFM32WG295* memory map is shown in Figure 2.2 (p. 9), with RAM and Flash sizes for the largest memory configuration.

3 Electrical Characteristics

3.1 Test Conditions

3.1.1 Typical Values

The typical data are based on $T_{AMB}=25^{\circ}\text{C}$ and $V_{DD}=3.0\text{ V}$, as defined in Table 3.2 (p. 10), by simulation and/or technology characterisation unless otherwise specified.

3.1.2 Minimum and Maximum Values

The minimum and maximum values represent the worst conditions of ambient temperature, supply voltage and frequencies, as defined in Table 3.2 (p. 10), by simulation and/or technology characterisation unless otherwise specified.

3.2 Absolute Maximum Ratings

The absolute maximum ratings are stress ratings, and functional operation under such conditions are not guaranteed. Stress beyond the limits specified in Table 3.1 (p. 10) may affect the device reliability or cause permanent damage to the device. Functional operating conditions are given in Table 3.2 (p. 10).

Table 3.1. Absolute Maximum Ratings

Symbol	Parameter	Condition	Min	Typ	Max	Unit
T_{STG}	Storage temperature range		-40		150 ¹	$^{\circ}\text{C}$
T_S	Maximum soldering temperature	Latest IPC/JEDEC J-STD-020 Standard			260	$^{\circ}\text{C}$
V_{DDMAX}	External main supply voltage		0		3.8	V
V_{IOPIN}	Voltage on any I/O pin		-0.3		$V_{DD}+0.3$	V

¹Based on programmed devices tested for 10000 hours at 150°C . Storage temperature affects retention of preprogrammed calibration values stored in flash. Please refer to the Flash section in the Electrical Characteristics for information on flash data retention for different temperatures.

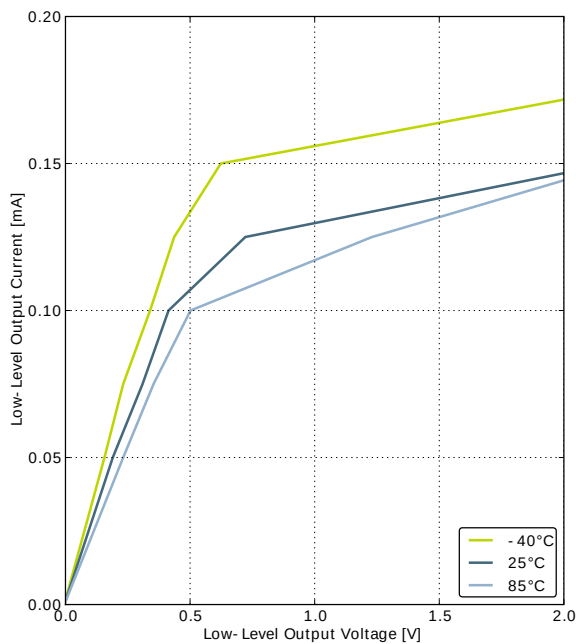
3.3 General Operating Conditions

3.3.1 General Operating Conditions

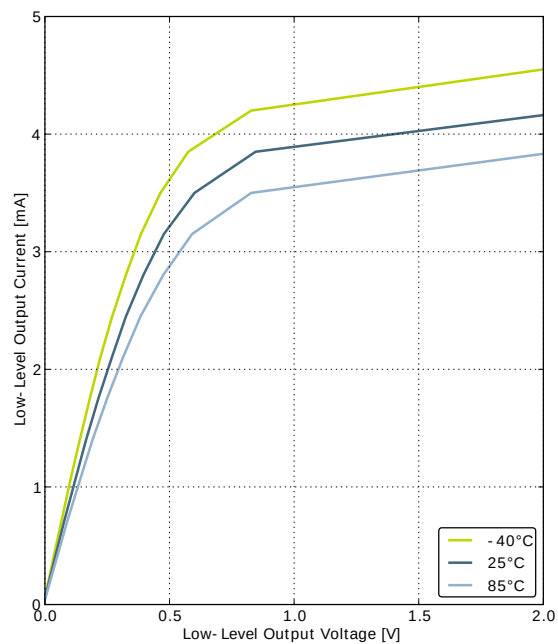
Table 3.2. General Operating Conditions

Symbol	Parameter	Min	Typ	Max	Unit
T_{AMB}	Ambient temperature range	-40		85	$^{\circ}\text{C}$
V_{DDOP}	Operating supply voltage	1.98		3.8	V
f_{APB}	Internal APB clock frequency			48	MHz
f_{AHB}	Internal AHB clock frequency			48	MHz

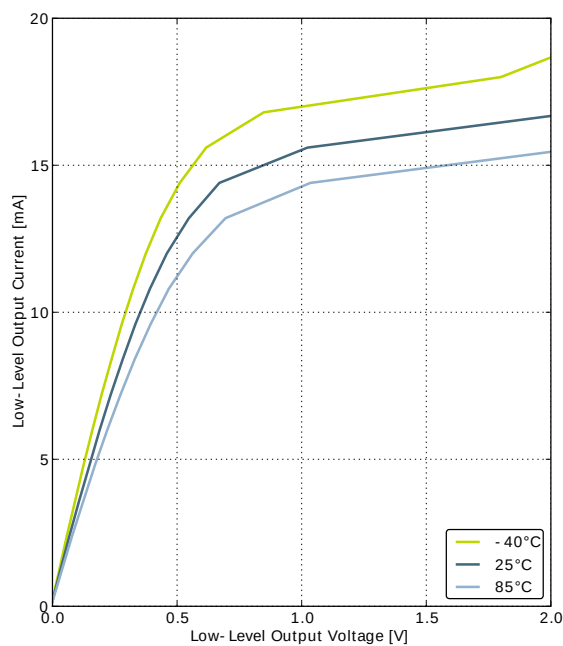
Figure 3.11. Typical Low-Level Output Current, 2V Supply Voltage



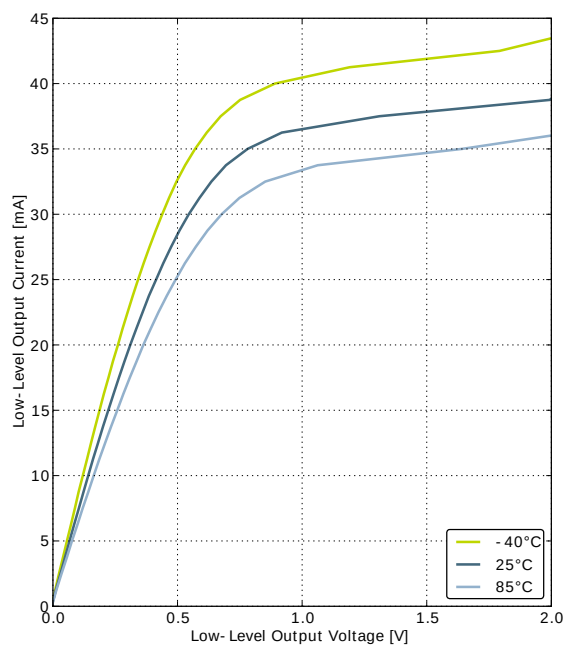
GPIO_Px_CTRL DRIVEMODE = LOWEST



GPIO_Px_CTRL DRIVEMODE = LOW

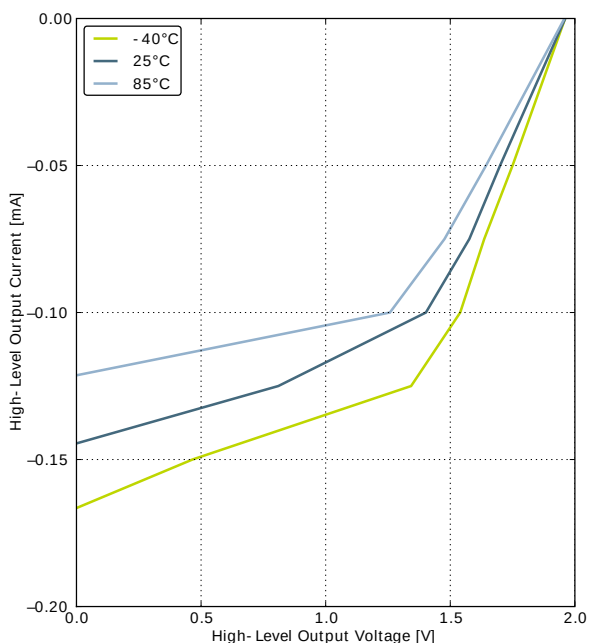


GPIO_Px_CTRL DRIVEMODE = STANDARD

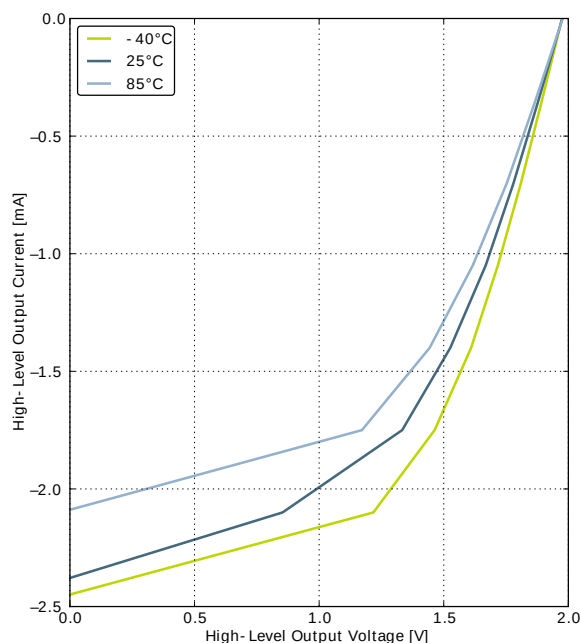


GPIO_Px_CTRL DRIVEMODE = HIGH

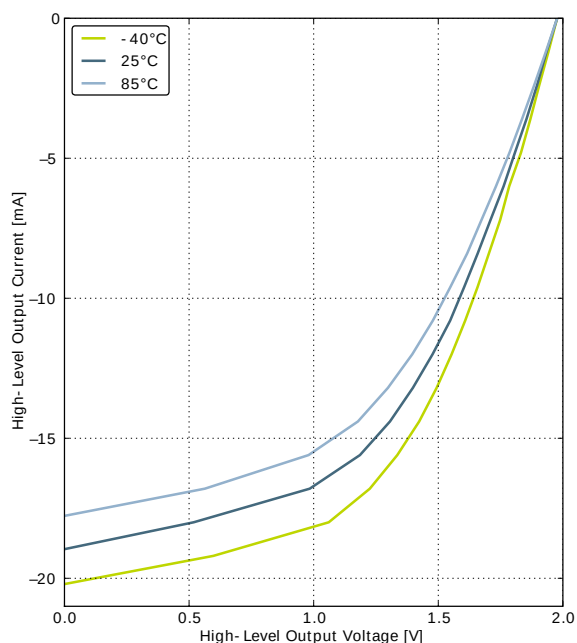
Figure 3.12. Typical High-Level Output Current, 2V Supply Voltage



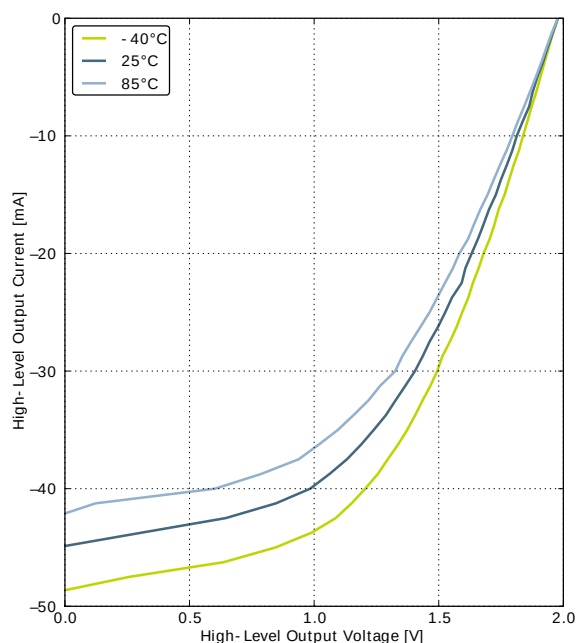
GPIO_Px_CTRL DRIVEMODE = LOWEST



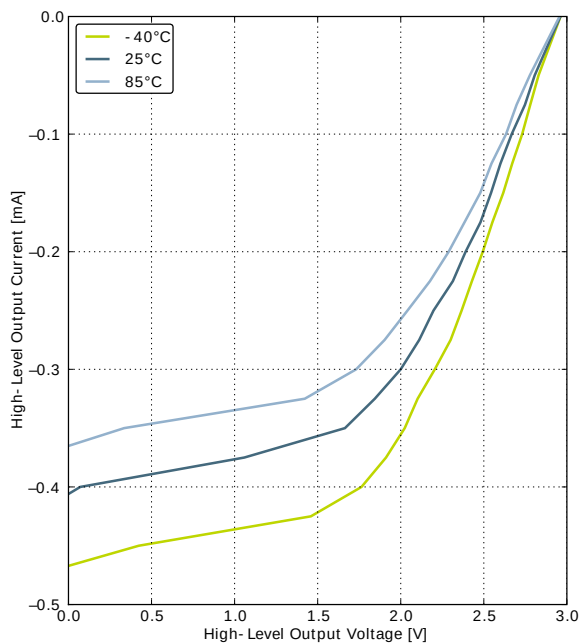
GPIO_Px_CTRL DRIVEMODE = LOW



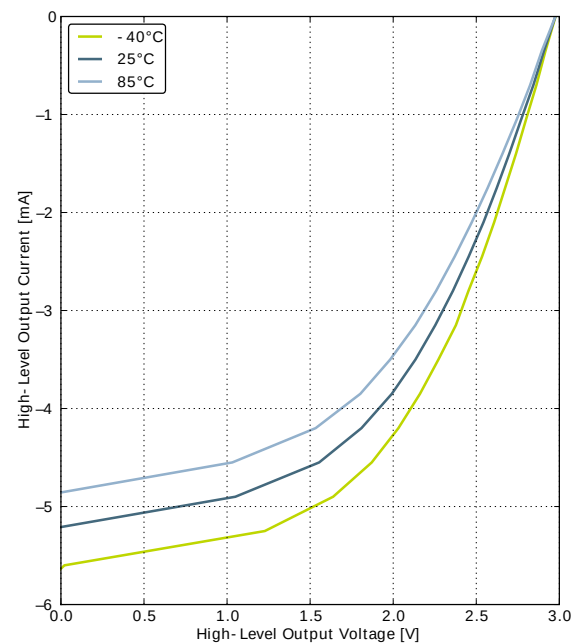
GPIO_Px_CTRL DRIVEMODE = STANDARD



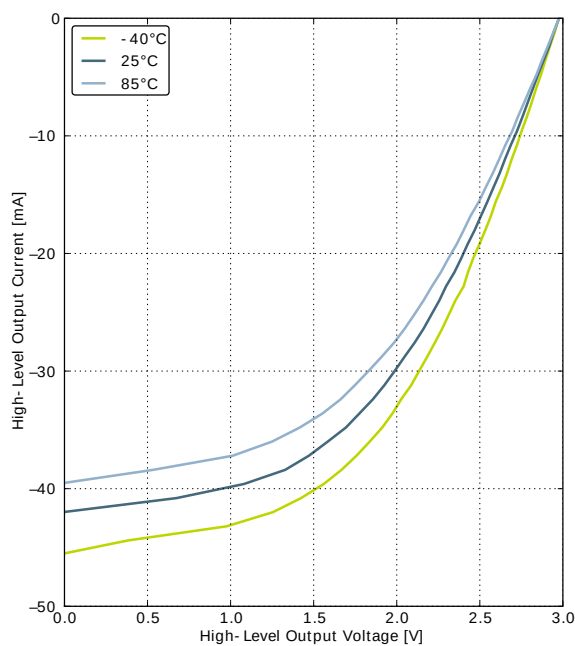
GPIO_Px_CTRL DRIVEMODE = HIGH

Figure 3.14. Typical High-Level Output Current, 3V Supply Voltage

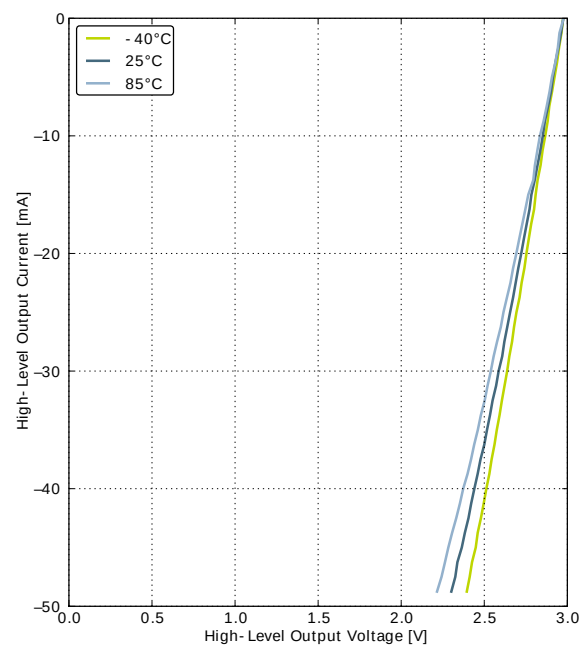
GPIO_Px_CTRL DRIVEMODE = LOWEST



GPIO_Px_CTRL DRIVEMODE = LOW



GPIO_Px_CTRL DRIVEMODE = STANDARD



GPIO_Px_CTRL DRIVEMODE = HIGH

3.9.3 LFRCO

Table 3.11. LFRCO

Symbol	Parameter	Condition	Min	Typ	Max	Unit
f_{LFRCO}	Oscillation frequency, $V_{DD}=3.0\text{ V}$, $T_{AMB}=25^{\circ}\text{C}$		31.29	32.768	34.28	kHz
t_{LFRCO}	Startup time not including software calibration			150		μs
I_{LFRCO}	Current consumption			300		nA
TUNESTEP _{LFRCO}	Frequency step for LSB change in TUNING value			1.5		%

Figure 3.17. Calibrated LFRCO Frequency vs Temperature and Supply Voltage

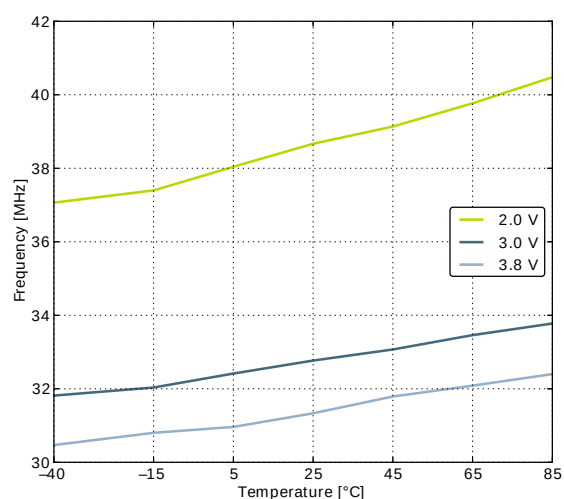
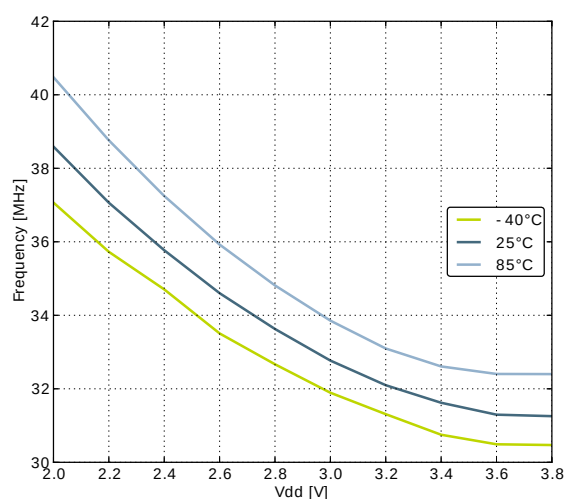
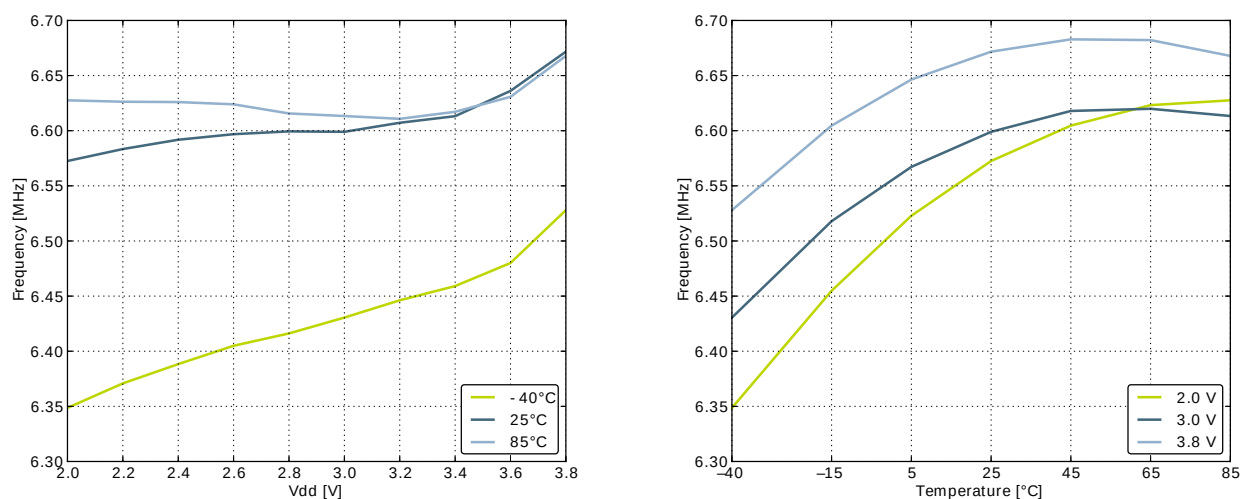
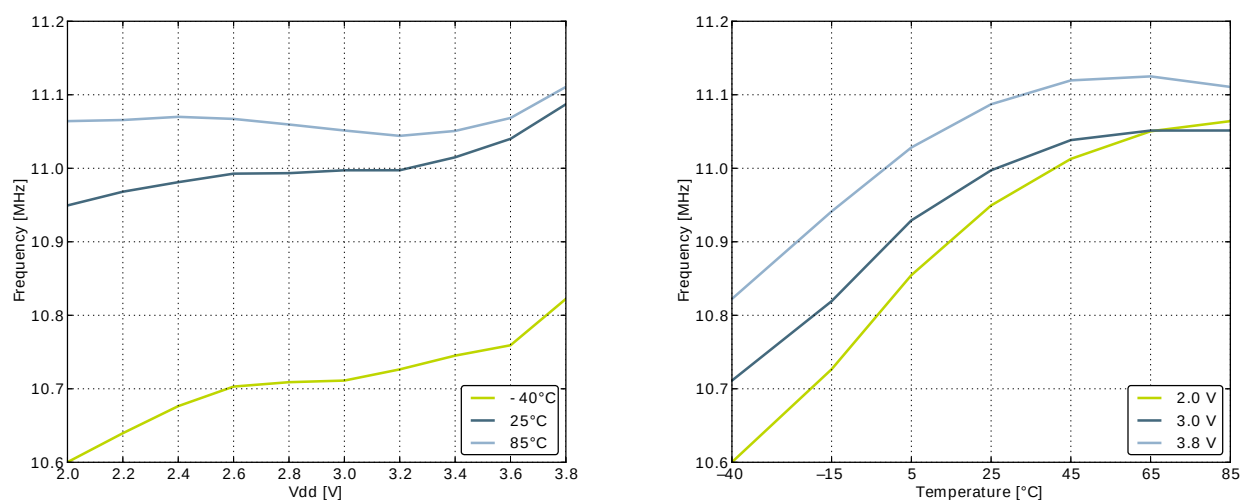
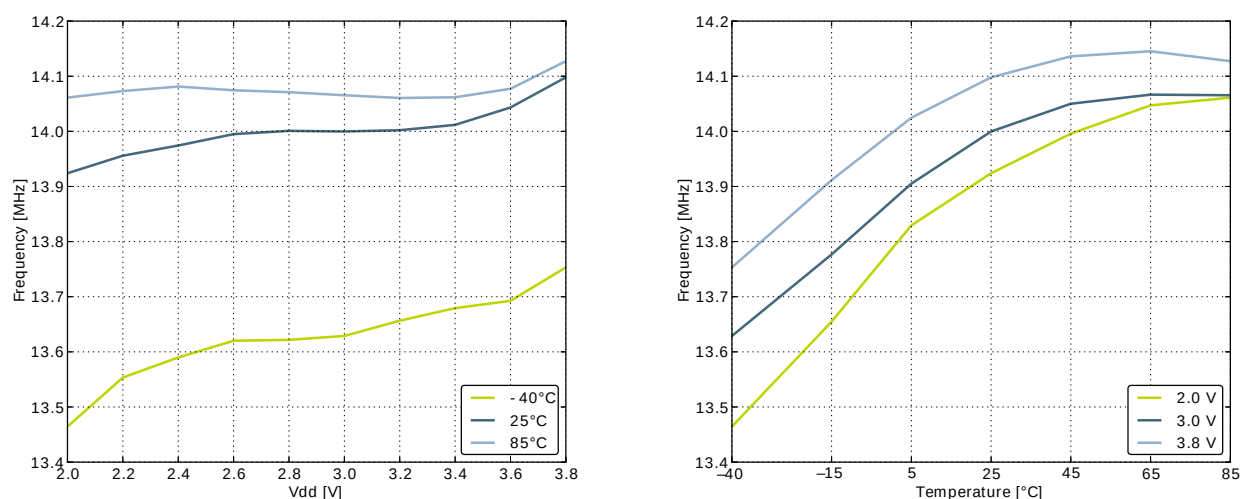
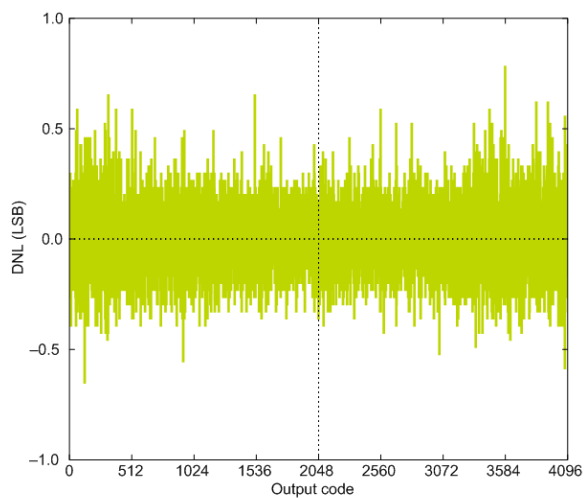
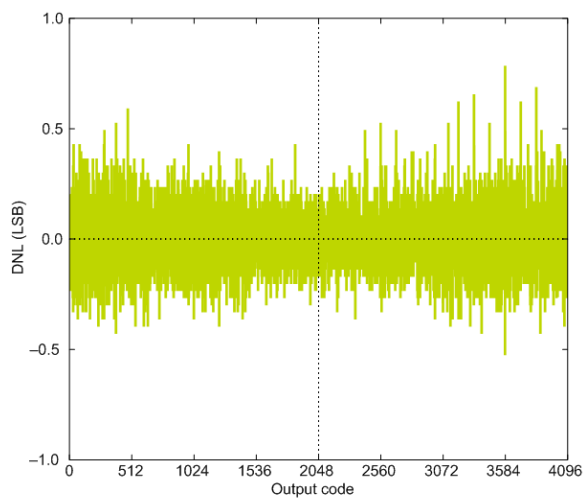
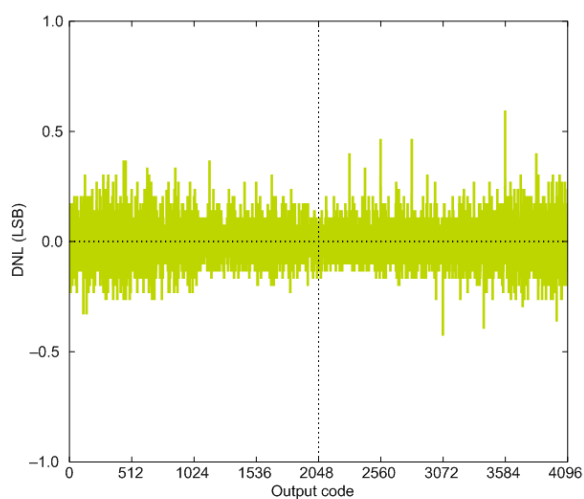
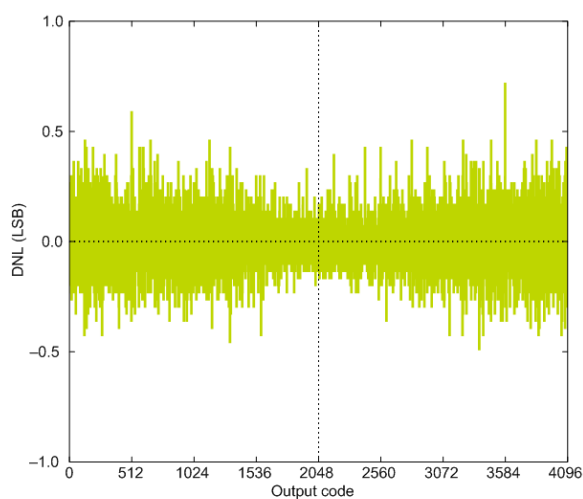
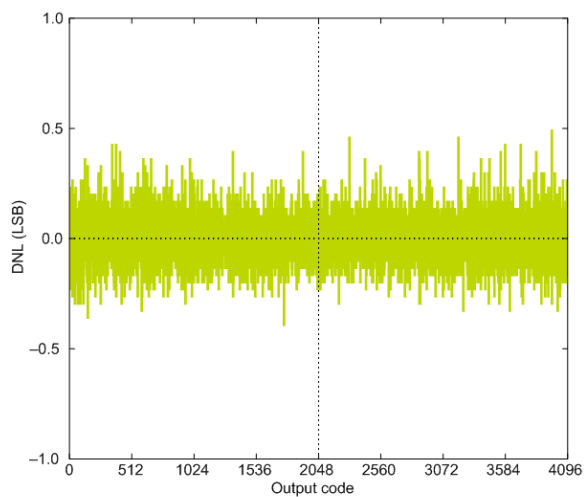


Figure 3.19. Calibrated HFRCO 7 MHz Band Frequency vs Supply Voltage and Temperature**Figure 3.20. Calibrated HFRCO 11 MHz Band Frequency vs Supply Voltage and Temperature****Figure 3.21. Calibrated HFRCO 14 MHz Band Frequency vs Supply Voltage and Temperature**

Symbol	Parameter	Condition	Min	Typ	Max	Unit
		1 MSamples/s, 12 bit, differential, internal 2.5V reference		64		dB
		1 MSamples/s, 12 bit, differential, 5V reference		54		dB
		1 MSamples/s, 12 bit, differential, V_{DD} reference		66		dB
		1 MSamples/s, 12 bit, differential, $2xV_{DD}$ reference		68		dB
		200 kSamples/s, 12 bit, single ended, internal 1.25V reference		61		dB
		200 kSamples/s, 12 bit, single ended, internal 2.5V reference		65		dB
		200 kSamples/s, 12 bit, single ended, V_{DD} reference		66		dB
		200 kSamples/s, 12 bit, differential, internal 1.25V reference		63		dB
		200 kSamples/s, 12 bit, differential, internal 2.5V reference		66		dB
		200 kSamples/s, 12 bit, differential, 5V reference		66		dB
		200 kSamples/s, 12 bit, differential, V_{DD} reference	62	66		dB
		200 kSamples/s, 12 bit, differential, $2xV_{DD}$ reference		69		dB
SFDR _{ADC}	Spurious-Free Dynamic Range (SFDR)	1 MSamples/s, 12 bit, single ended, internal 1.25V reference		64		dBc
		1 MSamples/s, 12 bit, single ended, internal 2.5V reference		76		dBc
		1 MSamples/s, 12 bit, single ended, V_{DD} reference		73		dBc
		1 MSamples/s, 12 bit, differential, internal 1.25V reference		66		dBc
		1 MSamples/s, 12 bit, differential, internal 2.5V reference		77		dBc
		1 MSamples/s, 12 bit, differential, V_{DD} reference		76		dBc
		1 MSamples/s, 12 bit, differential, $2xV_{DD}$ reference		75		dBc
		1 MSamples/s, 12 bit, differential, 5V reference		69		dBc
		200 kSamples/s, 12 bit, single ended, internal 1.25V reference		75		dBc
		200 kSamples/s, 12 bit, single ended, internal 2.5V reference		75		dBc
		200 kSamples/s, 12 bit, single ended, V_{DD} reference		76		dBc

Figure 3.28. ADC Differential Linearity Error vs Code, V_{dd} = 3V, Temp = 25°C**1.25V Reference****2.5V Reference****2XVDDVSS Reference****5VDIFF Reference****VDD Reference**

Symbol	Parameter	Condition	Min	Typ	Max	Unit
		$V_{out}=1V$, RESSEL=0, 0.1 Hz< f <1 MHz, OPAXHCMDIS=0		196		μV_{RMS}
		$V_{out}=1V$, RESSEL=0, 0.1 Hz< f <1 MHz, OPAXHCMDIS=1		229		μV_{RMS}
		RESSEL=7, 0.1 Hz< f <10 kHz, OPAXHCMDIS=0		1230		μV_{RMS}
		RESSEL=7, 0.1 Hz< f <10 kHz, OPAXHCMDIS=1		2130		μV_{RMS}
		RESSEL=7, 0.1 Hz< f <1 MHz, OPAXHCMDIS=0		1630		μV_{RMS}
		RESSEL=7, 0.1 Hz< f <1 MHz, OPAXHCMDIS=1		2590		μV_{RMS}

Figure 3.32. OPAMP Common Mode Rejection Ratio

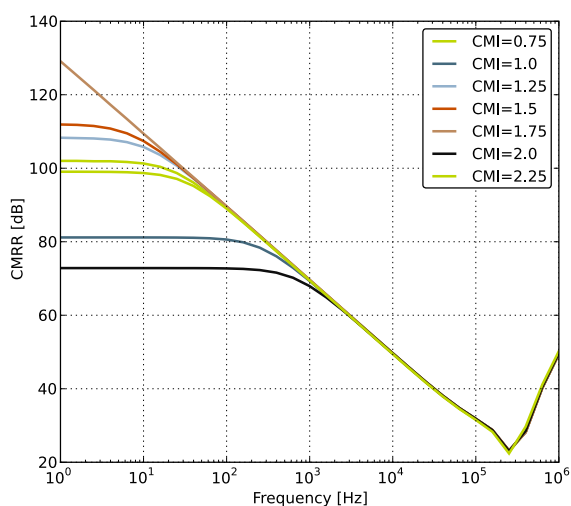
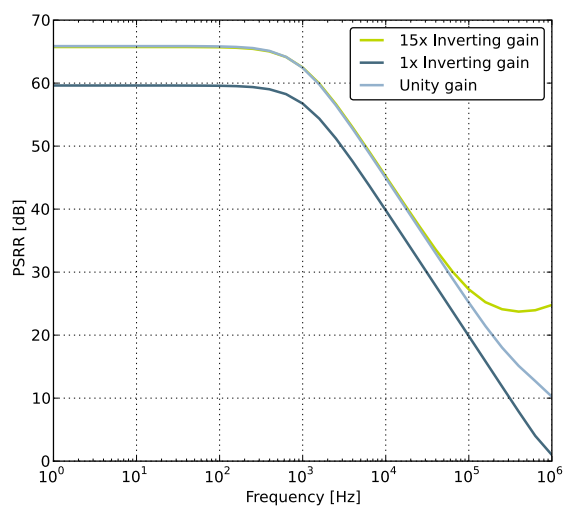


Figure 3.33. OPAMP Positive Power Supply Rejection Ratio



3.13 Analog Comparator (ACMP)

Table 3.18. ACMP

Symbol	Parameter	Condition	Min	Typ	Max	Unit
V_{ACMPIN}	Input voltage range		0		V_{DD}	V
V_{ACMPCM}	ACMP Common Mode voltage range		0		V_{DD}	V
I_{ACMP}	Active current	BIASPROG=0b0000, FULL-BIAS=0 and HALFBIAS=1 in ACMPn_CTRL register		0.1	0.4	μA
		BIASPROG=0b1111, FULL-BIAS=0 and HALFBIAS=0 in ACMPn_CTRL register		2.87	15	μA
		BIASPROG=0b1111, FULL-BIAS=1 and HALFBIAS=0 in ACMPn_CTRL register		195	520	μA
$I_{ACMPREF}$	Current consumption of internal voltage reference	Internal voltage reference off. Using external voltage reference		0		μA
		Internal voltage reference		5		μA
$V_{ACMPOFFSET}$	Offset voltage	BIASPROG= 0b1010, FULL-BIAS=0 and HALFBIAS=0 in ACMPn_CTRL register	-12	0	12	mV
$V_{ACMPHYST}$	ACMP hysteresis	Programmable		17		mV
R_{CSRES}	Capacitive Sense Internal Resistance	CSRESSEL=0b00 in ACMPn_INPUTSEL		39		kOhm
		CSRESSEL=0b01 in ACMPn_INPUTSEL		71		kOhm
		CSRESSEL=0b10 in ACMPn_INPUTSEL		104		kOhm
		CSRESSEL=0b11 in ACMPn_INPUTSEL		136		kOhm
$t_{ACMPSTART}$	Startup time				10	μs

The total ACMP current is the sum of the contributions from the ACMP and its internal voltage reference as given in Equation 3.1 (p. 47) . $I_{ACMPREF}$ is zero if an external voltage reference is used.

Total ACMP Active Current

$$I_{ACMPTOTAL} = I_{ACMP} + I_{ACMPREF} \quad (3.1)$$

3.14 Voltage Comparator (VCMP)

Table 3.19. VCMP

Symbol	Parameter	Condition	Min	Typ	Max	Unit
V _{VCMPIN}	Input voltage range			V _{DD}		V
V _{VCMPCM}	VCMP Common Mode voltage range			V _{DD}		V
I _{VCMP}	Active current	BIASPROG=0b0000 and HALFBIAS=1 in VCMPn_CTRL register		0.3	0.6	μA
		BIASPROG=0b1111 and HALFBIAS=0 in VCMPn_CTRL register. LPREF=0.		22	35	μA
t _{VCMPREF}	Startup time reference generator	NORMAL		10		μs
V _{VCMPOFFSET}	Offset voltage	Single ended		10		mV
		Differential		10		mV
V _{VCMPHYST}	VCMP hysteresis			61	210	mV
t _{VCMPSTART}	Startup time				10	μs

The V_{DD} trigger level can be configured by setting the TRIGLEVEL field of the VCMP_CTRL register in accordance with the following equation:

VCMP Trigger Level as a Function of Level Setting

$$V_{DD} \text{ Trigger Level} = 1.667V + 0.034 \times \text{TRIGLEVEL} \quad (3.2)$$

3.15 EBI

Figure 3.38. EBI Write Enable Timing

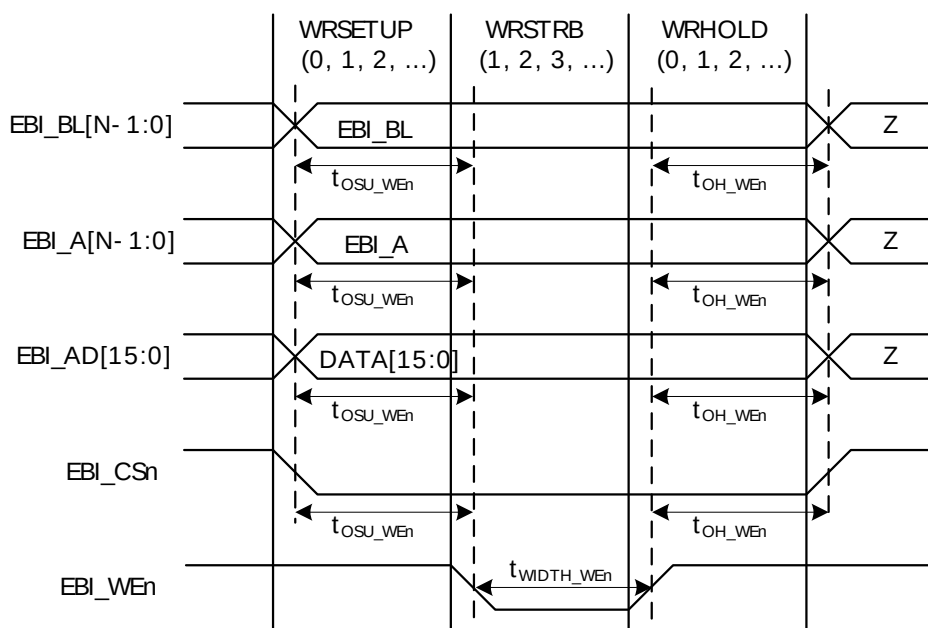


Table 3.20. EBI Write Enable Timing

Symbol	Parameter	Min	Typ	Max	Unit
$t_{OH_WEn}^{1\ 2\ 3\ 4}$	Output hold time, from trailing EBI_WEn/ EBI_NANDWEn edge to EBI_AD, EBI_A, EBI_CSn, EBI_BLn invalid	$-6.00 + (WRHOLD * t_{HFCORECLK})$			ns
$t_{OSU_WEn}^{1\ 2\ 3\ 4\ 5}$	Output setup time, from EBI_AD, EBI_A, EBI_CSn, EBI_BLn valid to leading EBI_WEn/ EBI_NANDWEn edge	$-14.00 + (WRSETUP * t_{HFCORECLK})$			ns
$t_{WIDTH_WEn}^{1\ 2\ 3\ 4\ 5}$	EBI_WEn/EBI_NANDWEn pulse width	$-7.00 + ((WRSTRB + 1) * t_{HFCORECLK})$			ns

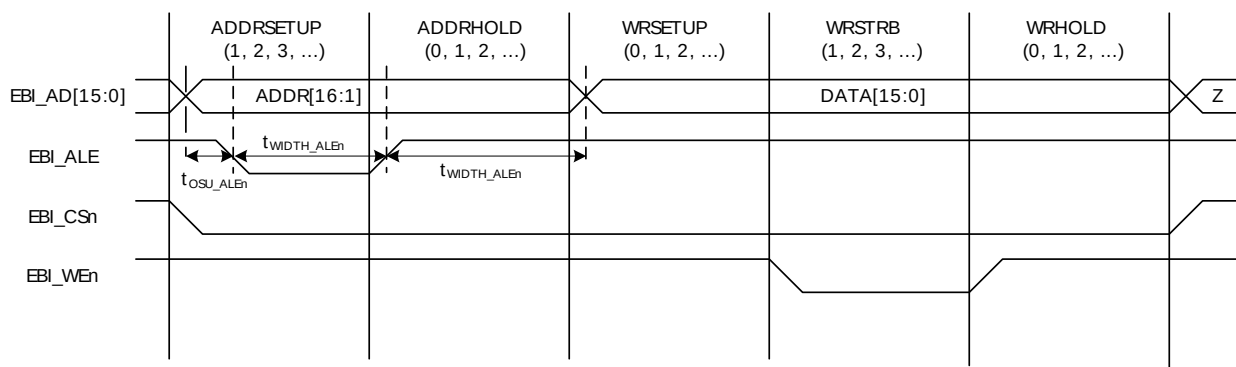
¹Applies for all addressing modes (figure only shows D16 addressing mode)

²Applies for both EBI_WEn and EBI_NANWEn (figure only shows EBI_WEn)

³Applies for all polarities (figure only shows active low signals)

⁴Measurement done at 10% and 90% of V_{DD} (figure shows 50% of V_{DD})

⁵ The figure shows the timing for the case that the half strobe length functionality is not used, i.e. HALFWE=0. The leading edge of EBI_WEn can be moved to the right by setting HALFWE=1. This decreases the length of t_{WIDTH_WEn} and increases the length of t_{OSU_WEn} by $1/2 * t_{HFCLKNODIV}$.

Figure 3.39. EBI Address Latch Enable Related Output Timing**Table 3.21. EBI Address Latch Enable Related Output Timing**

Symbol	Parameter	Min	Typ	Max	Unit
$t_{OH_ALEn}^{1\ 2\ 3\ 4}$	Output hold time, from trailing EBI_ALE edge to EBI_AD invalid	$-6.00 + (ADDRHOLD^5 * t_{HFCORECLK})$			ns
$t_{OSU_ALEn}^{1\ 2\ 4}$	Output setup time, from EBI_AD valid to leading EBI_ALE edge	$-13.00 + (0 * t_{HFCORECLK})$			ns
$t_{WIDTH_ALEn}^{1\ 2\ 3\ 4}$	EBI_ALEn pulse width	$-7.00 + (ADDRSETUP + 1) * t_{HFCORECLK}$			ns

¹Applies to addressing modes D8A24ALE and D16A16ALE (figure only shows D16A16ALE)

²Applies for all polarities (figure only shows active low signals)

³ The figure shows the timing for the case that the half strobe length functionality is not used, i.e. HALFALE=0. The trailing edge of EBI_ALE can be moved to the left by setting HALFALE=1. This decreases the length of t_{WIDTH_ALEn} and increases the length of t_{OH_ALEn} by $t_{HFCORECLK} - 1/2 * t_{HFCLKNODIV}$.

⁴Measurement done at 10% and 90% of V_{DD} (figure shows 50% of V_{DD})

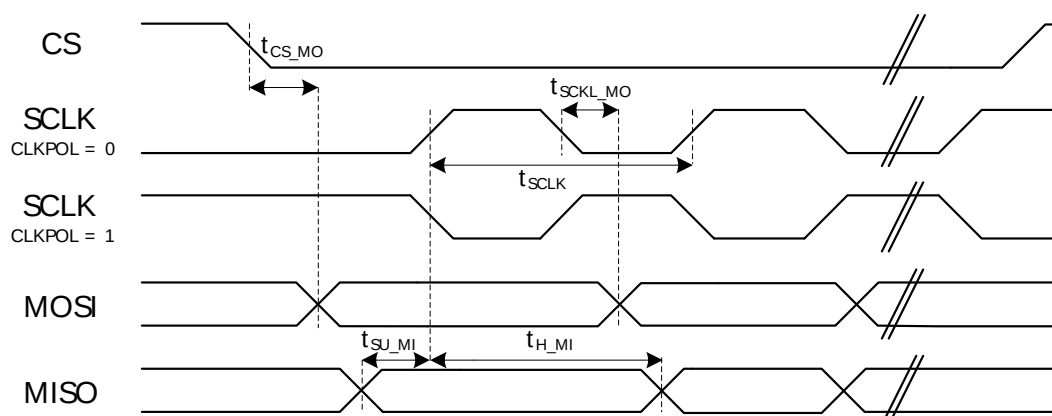
⁵Figure only shows a write operation. For a multiplexed read operation the address hold time is controlled via the RDSETUP state instead of via the ADDRHOLD state.

Table 3.27. I2C Fast-mode Plus (Fm+)

Symbol	Parameter	Min	Typ	Max	Unit
f_{SCL}	SCL clock frequency	0		1000 ¹	kHz
t_{LOW}	SCL clock low time	0.5			μs
t_{HIGH}	SCL clock high time	0.26			μs
$t_{SU,DAT}$	SDA set-up time	50			ns
$t_{HD,DAT}$	SDA hold time	8			ns
$t_{SU,STA}$	Repeated START condition set-up time	0.26			μs
$t_{HD,STA}$	(Repeated) START condition hold time	0.26			μs
$t_{SU,STO}$	STOP condition set-up time	0.26			μs
t_{BUF}	Bus free time between a STOP and a START condition	0.5			μs

¹For the minimum HPPERCLK frequency required in Fast-mode Plus, see the I2C chapter in the EFM32WG Reference Manual.

3.17 USART SPI

Figure 3.43. SPI Master Timing**Table 3.28. SPI Master Timing**

Symbol	Parameter	Condition	Min	Typ	Max	Unit
$t_{SCLK}^{1,2}$	SCLK period		$2 * t_{HPPER-CLK}$			ns
$t_{CS_MO}^{1,2}$	CS to MOSI		-2.00		2.00	ns
$t_{SCLK_MO}^{1,2}$	SCLK to MOSI		-1.00		3.00	ns
$t_{SU_MI}^{1,2}$	MISO setup time	IOVDD = 3.0 V	36.00			ns
$t_{H_MI}^{1,2}$	MISO hold time		-6.00			ns

¹Applies for both CLKPHA = 0 and CLKPHA = 1 (figure only shows CLKPHA = 0)

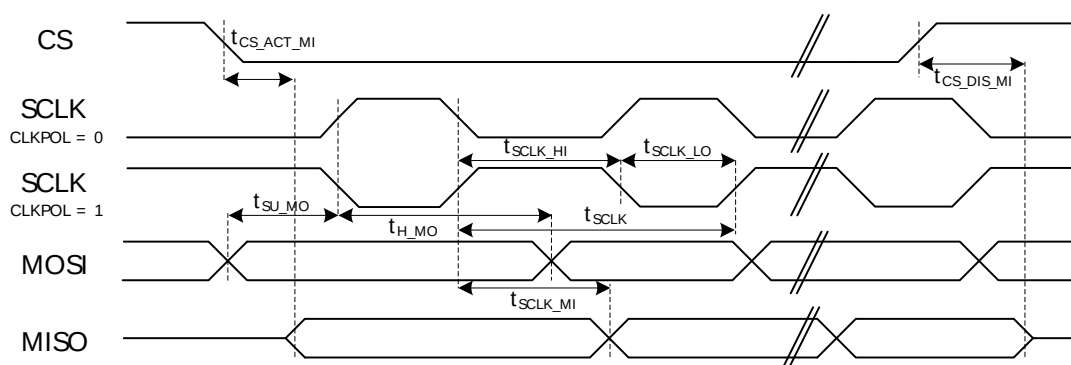
²Measurement done at 10% and 90% of V_{DD} (figure shows 50% of V_{DD})

Table 3.29. SPI Master Timing with SSSEARLY and SMSDELAY

Symbol	Parameter	Condition	Min	Typ	Max	Unit
$t_{\text{SCLK}}^{1\ 2}$	SCLK period		$2 * t_{\text{HFER-CLK}}$			ns
$t_{\text{CS_MO}}^{1\ 2}$	CS to MOSI		-2.00		2.00	ns
$t_{\text{SCLK_MO}}^{1\ 2}$	SCLK to MOSI		-1.00		3.00	ns
$t_{\text{SU_MI}}^{1\ 2}$	MISO setup time	IOVDD = 3.0 V	-32.00			ns
$t_{\text{H_MI}}^{1\ 2}$	MISO hold time		63.00			ns

¹Applies for both CLKPHA = 0 and CLKPHA = 1 (figure only shows CLKPHA = 0)

²Measurement done at 10% and 90% of V_{DD} (figure shows 50% of V_{DD})

Figure 3.44. SPI Slave Timing**Table 3.30. SPI Slave Timing**

Symbol	Parameter	Min	Typ	Max	Unit
$t_{\text{SCLK_sl}}^{1\ 2}$	SCKL period	$6 * t_{\text{HFER-CLK}}$			ns
$t_{\text{SCLK_hi}}^{1\ 2}$	SCLK high period	$3 * t_{\text{HFER-CLK}}$			ns
$t_{\text{SCLK_lo}}^{1\ 2}$	SCLK low period	$3 * t_{\text{HFER-CLK}}$			ns
$t_{\text{CS_ACT_MI}}^{1\ 2}$	CS active to MISO	5.00		35.00	ns
$t_{\text{CS_DIS_MI}}^{1\ 2}$	CS disable to MISO	5.00		35.00	ns
$t_{\text{SU_MO}}^{1\ 2}$	MOSI setup time	5.00			ns
$t_{\text{H_MO}}^{1\ 2}$	MOSI hold time	$2 + 2 * t_{\text{HFER-CLK}}$			ns
$t_{\text{SCLK_MI}}^{1\ 2}$	SCLK to MISO	$7 + t_{\text{HFER-CLK}}$		$42 + 2 * t_{\text{HFERCLK}}$	ns

¹Applies for both CLKPHA = 0 and CLKPHA = 1 (figure only shows CLKPHA = 0)

²Measurement done at 10% and 90% of V_{DD} (figure shows 50% of V_{DD})

Table 3.31. SPI Slave Timing with SSSEARLY and SMSDELAY

Symbol	Parameter	Min	Typ	Max	Unit
$t_{\text{SCLK_sl}}^{1\ 2}$	SCKL period	$6 * t_{\text{HFER-CLK}}$			ns

BGA120 Pin# and Name		Pin Alternate Functionality / Description				
Pin #	Pin Name	Analog	EBI	Timers	Communication	Other
H12	PE2	BU_VOUT	EBI_A09 #0	TIM3_CC2 #1	U1_TX #3	ACMP0_O #1
H13	PC7	ACMP0_CH7	EBI_A06 #0/1/2		LEU1_RX #0 I2C0_SCL #2	LES_CH7 #0 ETM_TD0 #2
J1	PD14				I2C0_SDA #3	
J2	PD15				I2C0_SCL #3	
J3	VSS	Ground				
J11	IOVDD_3	Digital IO power supply 3.				
J12	PC6	ACMP0_CH6	EBI_A05 #0/1/2		LEU1_TX #0 I2C0_SDA #2	LES_CH6 #0 ETM_TCLK #2
J13	DECOUPLE	Decouple output for on-chip voltage regulator. An external capacitance of size C _{DECOUPLE} is required at this pin.				
K1	PC0	ACMP0_CH0 DAC0_OUT0ALT #0/ OPAMP_OUT0ALT	EBI_A23 #0/1/2	TIM0_CC1 #4 PCNT0_S0IN #2	US0_TX #5 US1_TX #0 I2C0_SDA #4	LES_CH0 #0 PRS_CH2 #0
K2	PC1	ACMP0_CH1 DAC0_OUT0ALT #1/ OPAMP_OUT0ALT	EBI_A24 #0/1/2	TIM0_CC2 #4 PCNT0_S1IN #2	US0_RX #5 US1_RX #0 I2C0_SCL #4	LES_CH1 #0 PRS_CH3 #0
K3	IOVDD_4	Digital IO power supply 4.				
K11	VSS	Ground				
K12	VSS	Ground				
K13	PD8	BU_VIN				CMU_CLK1 #1
L1	PC2	ACMP0_CH2 DAC0_OUT0ALT #2/ OPAMP_OUT0ALT	EBI_A25 #0/1/2	TIM0_CDTI0 #4	US2_TX #0	LES_CH2 #0
L2	PC3	ACMP0_CH3 DAC0_OUT0ALT #3/ OPAMP_OUT0ALT	EBI_NANDREn #0/1/2	TIM0_CDTI1 #4	US2_RX #0	LES_CH3 #0
L3	PA7		EBI_CSTFT #0/1/2			
L4	IOVDD_5	Digital IO power supply 5.				
L5	VSS	Ground				
L6	VSS	Ground				
L7	IOVDD_6	Digital IO power supply 6.				
L8	PB9		EBI_A03 #0/1/2		U1_TX #2	
L9	PB10		EBI_A04 #0/1/2		U1_RX #2	
L10	PD0	ADC0_CH0 DAC0_OUT0ALT #4/ OPAMP_OUT0ALT OPAMP_OUT2 #1		PCNT2_S0IN #0	US1_TX #1	
L11	PD1	ADC0_CH1 DAC0_OUT1ALT #4/ OPAMP_OUT1ALT		TIM0_CC0 #3 PCNT2_S1IN #0	US1_RX #1	DBG_SWO #2
L12	PD4	ADC0_CH4 OPAMP_P2			LEU0_TX #0	ETM_TD2 #0/2
L13	PD7	ADC0_CH7 DAC0_N1 / OPAMP_N1		TIM1_CC1 #4 LETIM0_OUT1 #0 PCNT0_S1IN #3	US1_TX #2 I2C0_SCL #1	CMU_CLK0 #2 LES_ALTEX1 #0 ACMP1_O #2 ETM_TCLK #0
M1	PB7	LFXTAL_P		TIM1_CC0 #3	US0_TX #4 US1_CLK #0	
M2	PC4	ACMP0_CH4 DAC0_P0 /	EBI_A26 #0/1/2	TIM0_CDTI2 #4 LETIM0_OUT0 #3	US2_CLK #0 I2C1_SDA #0	LES_CH4 #0

Alternate	LOCATION							
Functionality	0	1	2	3	4	5	6	Description
EBI_REn	PF5	PF9	PF5					External Bus Interface (EBI) Read Enable output.
EBI_VSNC	PA10	PA10	PA10					External Bus Interface (EBI) TFT Vertical Synchronization pin.
EBI_WEn	PF4	PF8	PF4					External Bus Interface (EBI) Write Enable output.
ETM_TCLK	PD7	PF8	PC6	PA6				Embedded Trace Module ETM clock .
ETM_TD0	PD6	PF9	PC7	PA2				Embedded Trace Module ETM data 0.
ETM_TD1	PD3	PD13	PD3	PA3				Embedded Trace Module ETM data 1.
ETM_TD2	PD4	PB15	PD4	PA4				Embedded Trace Module ETM data 2.
ETM_TD3	PD5	PF3	PD5	PA5				Embedded Trace Module ETM data 3.
GPIO_EM4WU0	PA0							Pin can be used to wake the system up from EM4
GPIO_EM4WU1	PA6							Pin can be used to wake the system up from EM4
GPIO_EM4WU2	PC9							Pin can be used to wake the system up from EM4
GPIO_EM4WU3	PF1							Pin can be used to wake the system up from EM4
GPIO_EM4WU4	PF2							Pin can be used to wake the system up from EM4
GPIO_EM4WU5	PE13							Pin can be used to wake the system up from EM4
HFX TAL_N	PB14							High Frequency Crystal negative pin. Also used as external optional clock input pin.
HFX TAL_P	PB13							High Frequency Crystal positive pin.
I2C0_SCL	PA1	PD7	PC7	PD15	PC1	PF1	PE13	I2C0 Serial Clock Line input / output.
I2C0_SDA	PA0	PD6	PC6	PD14	PC0	PF0	PE12	I2C0 Serial Data input / output.
I2C1_SCL	PC5	PB12	PE1					I2C1 Serial Clock Line input / output.
I2C1_SDA	PC4	PB11	PE0					I2C1 Serial Data input / output.
LES_ALTEX0	PD6							LESENSE alternate exite output 0.
LES_ALTEX1	PD7							LESENSE alternate exite output 1.
LES_ALTEX2	PA3							LESENSE alternate exite output 2.
LES_ALTEX3	PA4							LESENSE alternate exite output 3.
LES_ALTEX4	PA5							LESENSE alternate exite output 4.
LES_ALTEX5	PE11							LESENSE alternate exite output 5.
LES_ALTEX6	PE12							LESENSE alternate exite output 6.
LES_ALTEX7	PE13							LESENSE alternate exite output 7.
LES_CH0	PC0							LESENSE channel 0.
LES_CH1	PC1							LESENSE channel 1.
LES_CH2	PC2							LESENSE channel 2.
LES_CH3	PC3							LESENSE channel 3.
LES_CH4	PC4							LESENSE channel 4.
LES_CH5	PC5							LESENSE channel 5.
LES_CH6	PC6							LESENSE channel 6.
LES_CH7	PC7							LESENSE channel 7.
LES_CH8	PC8							LESENSE channel 8.
LES_CH9	PC9							LESENSE channel 9.
LES_CH10	PC10							LESENSE channel 10.
LES_CH11	PC11							LESENSE channel 11.

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